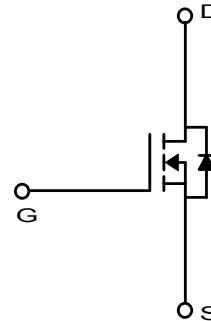
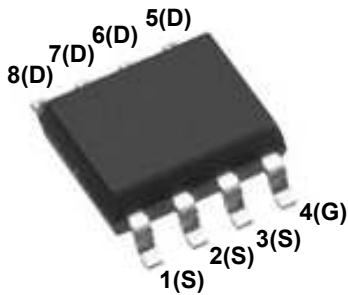


General Description

The MDS1528 uses advanced MagnaChip's MOSFET Technology, which provides high performance in on-state resistance, fast switching performance and excellent quality. MDS1528 is suitable for DC/DC converter and general purpose applications.

Features

- $V_{DS} = 30V$
- $I_D = 11.9A @ V_{GS} = 10V$
- $R_{DS(ON)} < 18.8m\Omega @ V_{GS} = 10V$
 $< 27.8m\Omega @ V_{GS} = 4.5V$
- 100% UIL Tested
- 100% Rg Tested



Absolute Maximum Ratings (Ta = 25°C)

Characteristics		Symbol	Rating	Unit
Drain-Source Voltage		V_{DSS}	30	V
Gate-Source Voltage		V_{GSS}	± 20	V
Continuous Drain Current ⁽¹⁾	$T_C = 25^\circ C$	I_D	11.9	A
	$T_C = 70^\circ C$		9.5	
	$T_A = 25^\circ C$		8.7 ⁽³⁾	
	$T_A = 70^\circ C$		6.9 ⁽³⁾	
Pulsed Drain Current		I_{DM}	40	A
Power Dissipation	$T_C = 25^\circ C$	P_D	4.7	W
	$T_C = 70^\circ C$		3.0	
	$T_A = 25^\circ C$		2.5 ⁽³⁾	
	$T_A = 70^\circ C$		1.6 ⁽³⁾	
Single Pulse Avalanche Energy ⁽²⁾		E_{AS}	20	mJ
Junction and Storage Temperature Range		T_J, T_{stg}	-55~150	°C

Thermal Characteristics

Characteristics	Symbol	Rating	Unit
Thermal Resistance, Junction-to-Ambient ⁽¹⁾	$R_{\theta JA}$	50	°C/W
Thermal Resistance, Junction-to-Case	$R_{\theta JC}$	26.4	

Ordering Information

Part Number	Temp. Range	Package	Packing	Quantity	Rohs Status
MDS1528URH	-55~150°C	SOIC-8	Tape & Reel	3000 units	Halogen Free

Electrical Characteristics (T_J = 25°C)

Characteristics	Symbol	Test Condition	Min	Typ	Max	Unit
Static Characteristics						
Drain-Source Breakdown Voltage	BV _{DSS}	I _D = 250μA, V _{GS} = 0V	30	-	-	V
Gate Threshold Voltage	V _{GS(th)}	V _{DS} = V _{GS} , I _D = 250μA	1.3	1.9	2.7	
Drain Cut-Off Current	I _{DSS}	V _{DS} = 30V, V _{GS} = 0V T _J =55°C	-	-	1	μA
Gate Leakage Current	I _{GSS}	V _{GS} = ±20V, V _{DS} = 0V	-	-	±0.1	
Drain-Source ON Resistance	R _{DS(ON)}	V _{GS} = 10V, I _D = 6A T _J =125°C	-	16.3	18.8	mΩ
		V _{GS} = 4.5V, I _D = 5A	-	23.2	27.8	
Forward Transconductance	g _{fs}	V _{DS} = 5V, I _D = 6A	-	20	-	S
Dynamic Characteristics						
Total Gate Charge	Q _{g(10V)}	V _{DS} = 15.0V, I _D = 6A, V _{GS} = 10V	5.1	7.3	9.5	nC
Total Gate Charge	Q _{g(4.5V)}		2.5	3.6	4.6	
Gate-Source Charge	Q _{gs}		-	1.6	-	
Gate-Drain Charge	Q _{gd}		-	1.3	-	
Input Capacitance	C _{iss}	V _{DS} = 15.0V, V _{GS} = 0V, f = 1.0MHz	317	453	589	pF
Reverse Transfer Capacitance	C _{rss}		30	43	56	
Output Capacitance	C _{oss}		62	88	115	
Turn-On Delay Time	t _{d(on)}	V _{GS} = 10V, V _{DS} = 15.0V, I _D = 6A, R _G = 3.0Ω	-	5.5	-	ns
Rise Time	t _r		-	3.1	-	
Turn-Off Delay Time	t _{d(off)}		-	14.0	-	
Fall Time	t _f		-	2.8	-	
Gate Resistance	R _g	f=1 MHz	1.0	3.2	6.0	Ω
Drain-Source Body Diode Characteristics						
Source-Drain Diode Forward Voltage	V _{SD}	I _S = 6A, V _{GS} = 0V	-	0.84	1.1	V
Body Diode Reverse Recovery Time	t _{rr}	I _F = 6A, di/dt = 100A/μs	-	15.9	23.8	ns
Body Diode Reverse Recovery Charge	Q _{rr}		-	8.7	13.1	nC

Note :

- Surface mounted FR-4 board by JEDEC (jesd51-7)
- E_{AS} is tested at starting T_J = 25°C, L = 0.1mH, I_{AS} = 10.8A, V_{DD} = 27V, V_{GS} = 10V
- T < 10sec

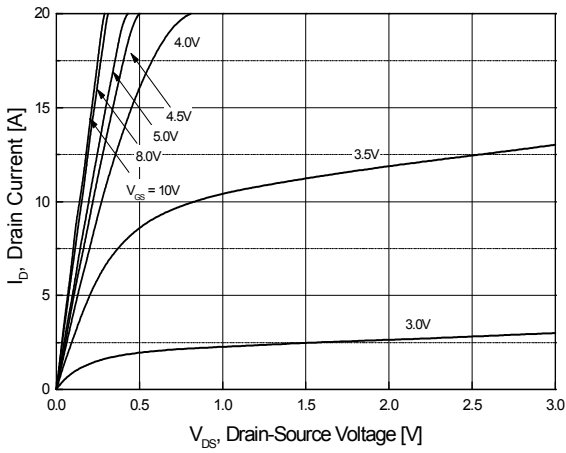


Fig.1 On-Region Characteristics

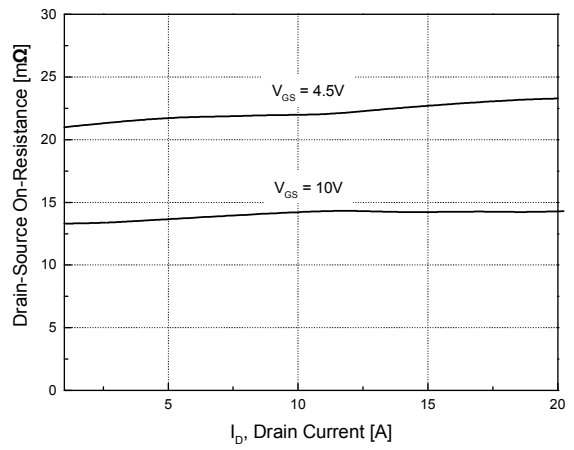


Fig.2 On-Resistance Variation with Drain Current and Gate Voltage

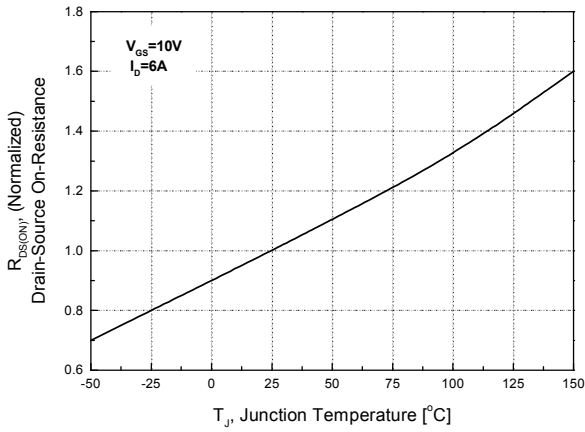


Fig.3 On-Resistance Variation with Temperature

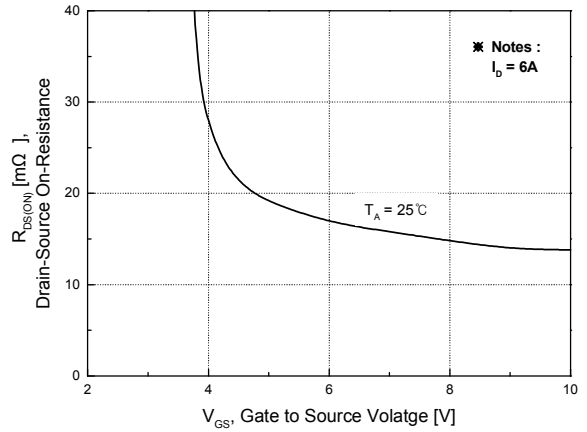


Fig.4 On-Resistance Variation with Gate to Source Voltage

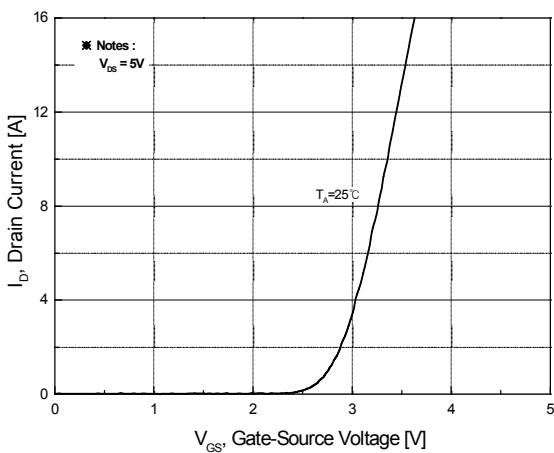


Fig.5 Transfer Characteristics

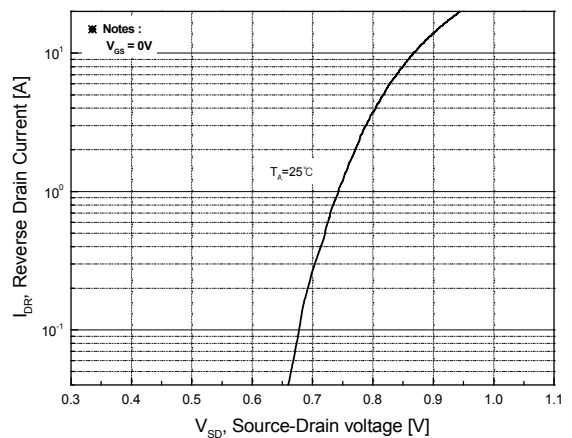


Fig.6 Body Diode Forward Voltage Variation with Source Current and Temperature

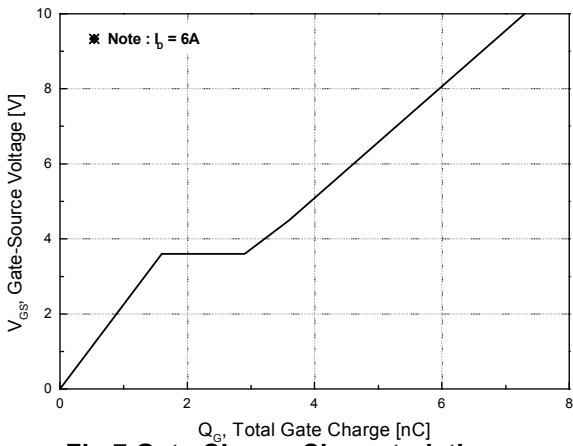


Fig.7 Gate Charge Characteristics

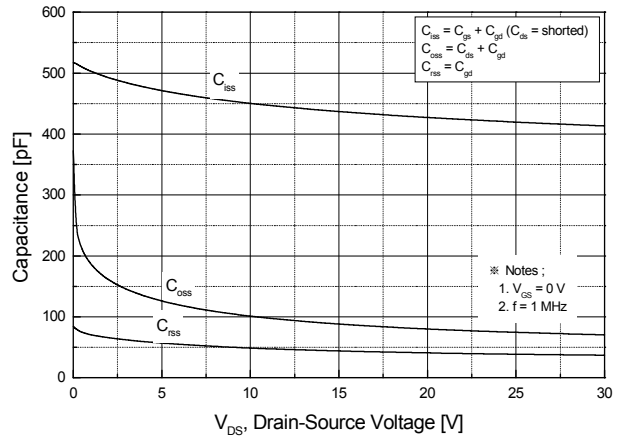


Fig.8 Capacitance Characteristics

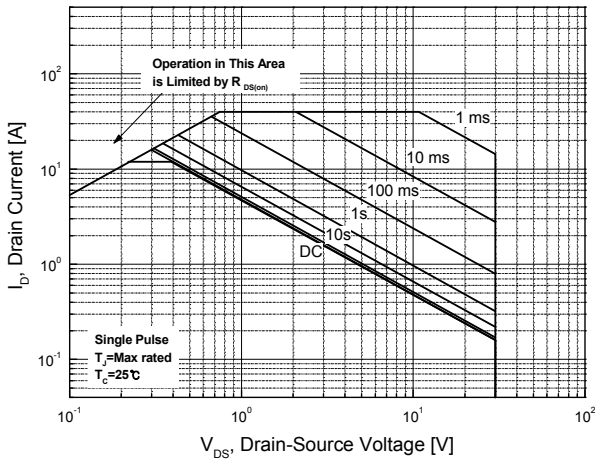


Fig.9 Maximum Safe Operating Area

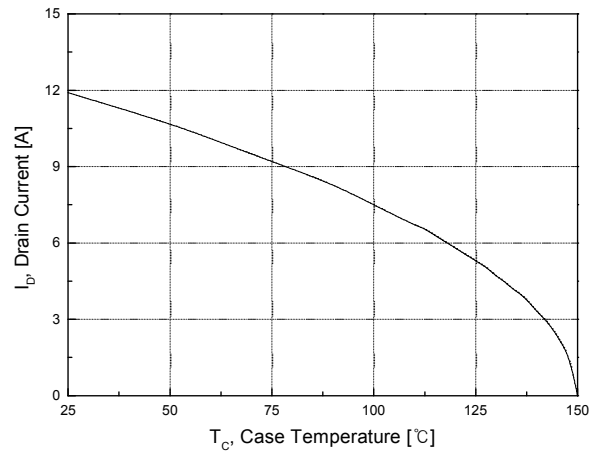


Fig.10 Maximum Drain Current vs. Case Temperature

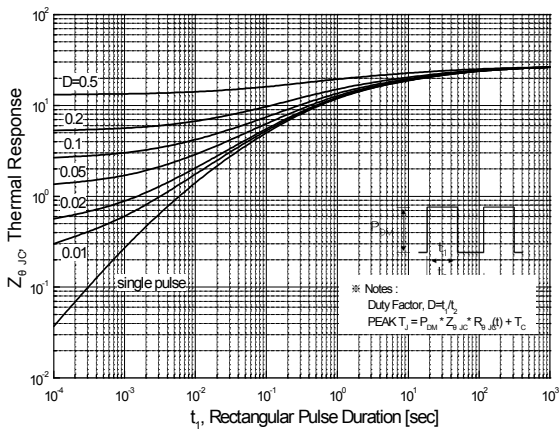
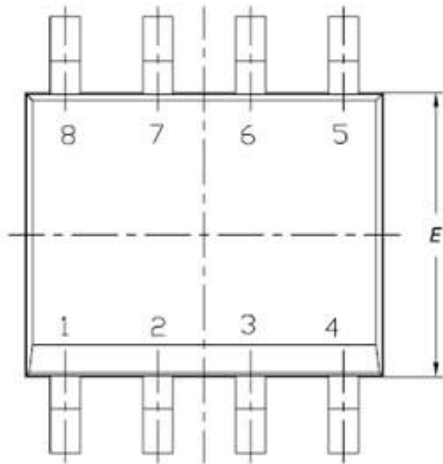


Fig.11 Transient Thermal Response Curve

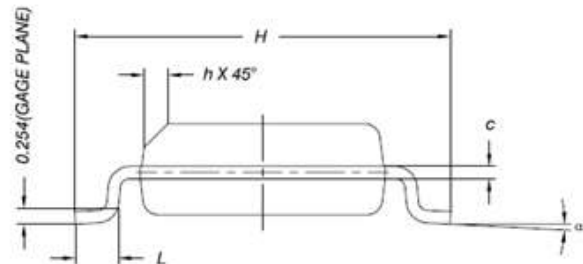
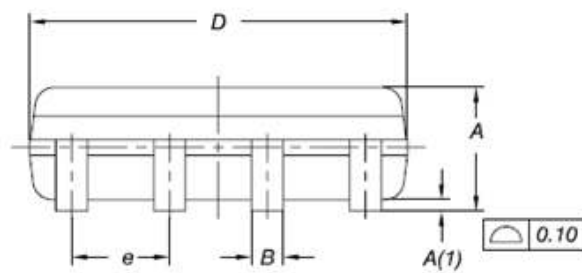
Physical Dimensions

8 Leads, SOIC

Dimensions are in millimeters unless otherwise specified



Symbol	Min	Nom	Max
A	-	-	1.75
A(1)	0.10	-	0.25
B	0.31	-	0.51
C	0.10	-	0.25
D	4.9 BSC		
E	3.9 BSC		
e	1.27 BSC		
H	6.0 BSC		
L	0.40	-	1.27
a	0	-	8
h	0.250	-	0.500
L2(Gage plane)	0.25 BSC		



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